8 A hyperfast rectifier diode

Rev. 01 — 23 February 2010

Product data sheet

1. Product profile

1.1 General description

Hyperfast epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package specifically for use in CCM PFC applications for reduced switching losses.

1.2 Features and benefits

- Allows use of smaller MOSFETs and heatsinks
- Isolated package
- Low reverse recovery current

1.3 Applications

- Continuous Current Mode (CCM) Power Factor Correction (PFC)
- Desk top computer power supplies
- Flat panel TV power supplies

1.4 Quick reference data

Table 1. Quick reference

- Low thermal resistance
- Reduces switching losses in associated MOSFET
- Superfast switching
- Power supply adapters
- Server power supplies
- Telecom power supplies

Table 1.	Quick reference					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	-	600	V
I _{F(AV)}	average forward current	square-wave pulse; $\delta = 0.5$; T _h ≤ 93 °C; see <u>Figure 1</u> and <u>2</u>	-	-	8	А
I _{FSM}	non-repetitive peak forward current	$T_{j(init)} = 25 \text{ °C}; t_p = 10 \text{ ms};$ sine-wave pulse	-	-	110	A
		$T_{j(init)} = 25 \text{ °C}; t_p = 8.3 \text{ ms};$ sine-wave pulse	-	-	120	A
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	2.5	3	K/W



Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic	characteristics					
t _{rr}	reverse recovery time	$\label{eq:IF} \begin{array}{l} I_F = 8 \text{ A}; V_R = 400 \text{ V}; \\ \text{d}I_F/\text{d}t = 200 \text{ A}/\mu\text{s}; T_j = 25 ^\circ\text{C}; \\ \text{see } \underline{\text{Figure 6}} \end{array}$	-	12.5	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V};$ $dI_F/dt = 200 \text{ A}/\mu\text{s}; T_j = 125 \text{ °C};$ see <u>Figure 6</u> and <u>7</u>	-	21	-	ns
Qr	recovered charge	$I_F = 8 A; V_R = 400 V;$ $dI_F/dt = 200 A/\mu s; T_j = 125 °C;$ see <u>Figure 5</u> and <u>6</u>	-	40	-	nC
Static ch	aracteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; see <u>Figure 4</u>	-	2.35	3.2	V
		I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u>	-	2	2.4	V

Table 1. Quick reference ...continued

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	К	cathode		
2	А	anode	mb	K — A 001aaa020
mb	n.c.	mounting base; isolated		
			SOD113 (TO-220F)	

3. Ordering information

Table 3. Ordering information					
Type number	Package				
	Name	Description	Version		
BYC58X-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113		

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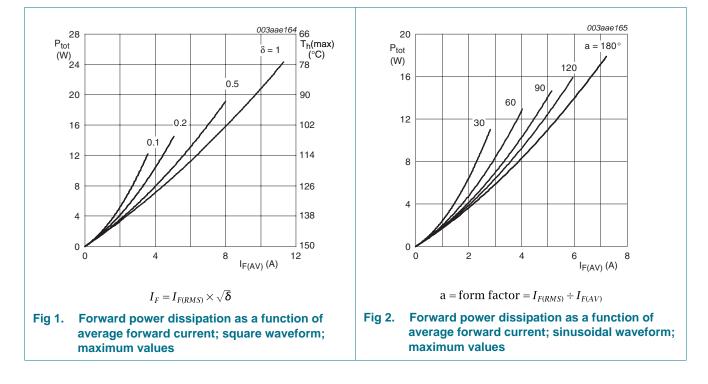
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4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{RRM}	repetitive peak reverse voltage		-	600	V
V _{RWM}	crest working reverse voltage		-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; δ = 0.5; T _h ≤ 93 °C; see Figure 1 and 2	-	8	А
I _{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5; t _p = 25 µs	-	16	А
I _{FSM}	non-repetitive peak	t _p = 10 ms; sine-wave pulse; T _{j(init)} = 25 °C	-	110	А
1	forward current	t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	120	А
T _{stg}	storage temperature		-40	150	°C
T _i	junction temperature		-	150	°C



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Thermal characteristics 5.

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Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-h)}	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	2.5	3	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	in free air	-	55	-	K/W

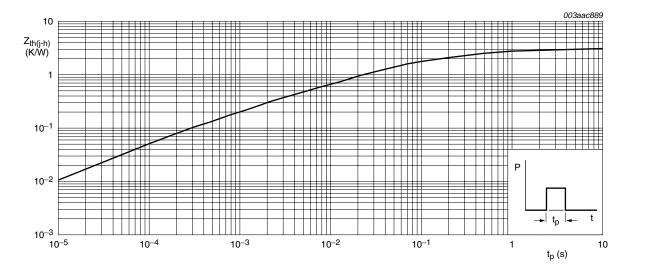


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

Isolation characteristics 6.

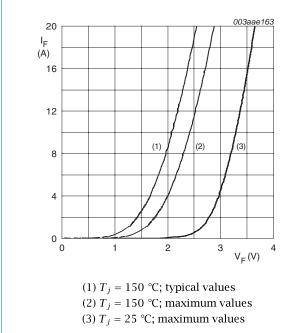
Table 6. **Isolation characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{isol(RMS)}	RMS isolation voltage	50 Hz \leq f \leq 60 Hz; RH \leq 65 %; from all pins to external heatsink; sinusoidal waveform; clean and dust free	-	-	2500	V
C _{isol}	isolation capacitance	f = 1 MHz; from cathode to external heatsink	-	10	-	pF

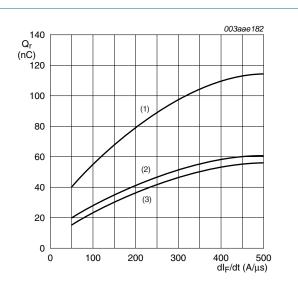
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7. Characteristics

Table 7.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _F	forward voltage	I _F = 8 A; T _j = 25 °C; see <u>Figure 4</u>	-	2.35	3.2	V
		I _F = 8 A; T _j = 150 °C; see <u>Figure 4</u>	-	2	2.4	V
I _R	reverse current	V _R = 600 V; T _j = 25 °C	-	-	150	μA
Dynamic	characteristics					
Qr	recovered charge	I_F = 8 A; V_R = 400 V; dI _F /dt = 200 A/µs; T _j = 125 °C; see <u>Figure 5</u> and <u>6</u>	-	40	-	nC
t _{rr}	reverse recovery time	I _F = 8 A; V _R = 400 V; dI _F /dt = 200 A/μs; T _j = 25 °C; see <u>Figure 6</u>	-	12.5	-	ns
		$I_F = 8 \text{ A}; V_R = 400 \text{ V}; \text{ d}_F/\text{d}t = 200 \text{ A}/\mu\text{s};$ $T_j = 125 \text{ °C}; \text{ see } \frac{\text{Figure 6}}{1000 \text{ g}} \text{ and } \frac{7}{100000000000000000000000000000000000$	-	21	-	ns
I _{RM}	peak reverse recovery current	$I_F = 8 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 200 \text{ A}/\mu\text{s};$ $T_i = 125 \text{ °C}$	-	4	5.5	А







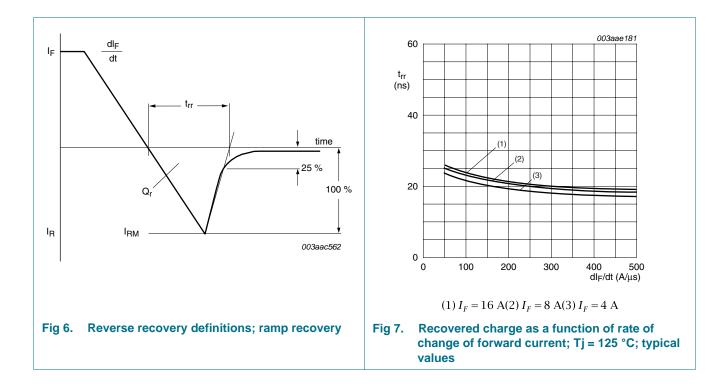
(1)
$$I_F = 16 \text{ A}(2) I_F = 8 \text{ A}(3) I_F = 4 \text{ A}$$

Fig 5. Recovered charge as a function of rate of change of forward current; Tj = 125 °C; typical values

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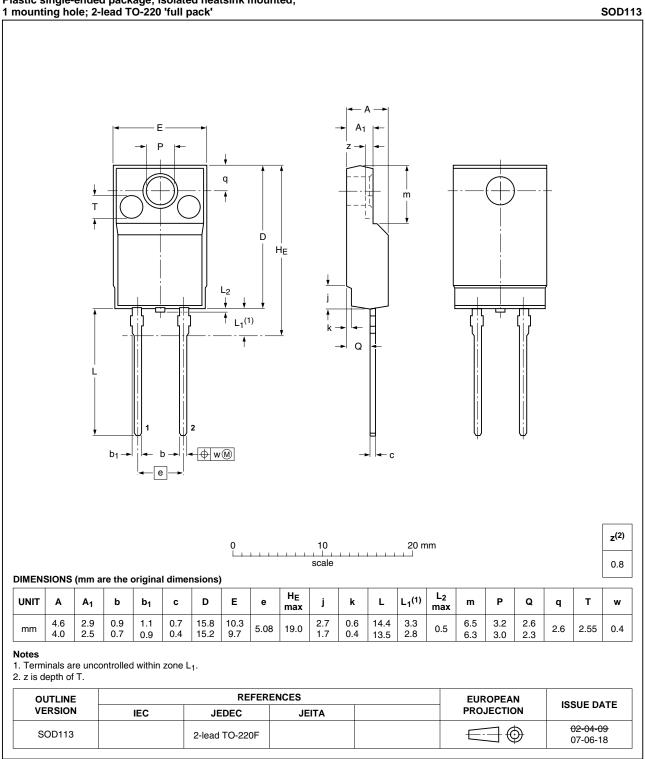
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Package outline 8.



Plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 'full pack'

Package outline SOD113 (TO-220F) Fig 8.

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9. Revision history

Table 8. Revision his	Revision history				
Document ID	Release date	Data sheet status	Change notice	Supersedes	
BYC58X-600_1	20100223	Product data sheet	-	-	

10. Legal information

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Document status [1][2]	Product status ^[3]	Definition
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